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<ul> <li>State-of-the-Art Advanced BiCMOS</li></ul>	SN54LVT244B J OR W PACKAGE
Technology (ABT) Design for 3.3-V	SN74LVT244B DB, DW, OR PW PACKAGE
Operation and Low Static-Power	(TOP VIEW)
Dissipation	
<ul> <li>High-Impedance State During Power Up</li></ul>	1A1 [] 2 19 ] 2OE
and Power Down	2Y4 [] 3 18 [] 1Y1
<ul> <li>Support Mixed-Mode Signal Operation (5-V</li></ul>	1A2 [] 4 17 [] 2A4
Input and Output Voltages With 3.3-V V <sub>CC</sub> )	2Y3 [] 5 16 [] 1Y2
<ul> <li>Support Unregulated Battery Operation</li></ul>	1A3 [] 6 15 [] 2A3
Down to 2.7 V	2Y2 [] 7 14 [] 1Y3
<ul> <li>Typical V<sub>OLP</sub> (Output Ground Bounce)</li> <li>&lt;0.8 V at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C</li> </ul>	1A4 [] 8 13 [] 2A2 2Y1 [] 9 12 [] 1Y4
<ul> <li>I<sub>off</sub> and Power-Up 3-State Support Hot Insertion</li> </ul>	GND [10 11] 2A1
<ul> <li>Latch-Up Performance Exceeds 100 mA Per</li></ul>	SN54LVT244B FK PACKAGE
JESD 78, Class II	(TOP VIEW)
<ul> <li>ESD Protection Exceeds JESD 22</li> <li>2000-V Human-Body Model (A114-A)</li> <li>200 V Machine Model (A115-A)</li> </ul>	20E 20E 20E

- 200-V Machine Model (A115-A)
- 1000-V Charged-Device Model (C101) Package Options Include Plastic
- Small-Outline (DW), Shrink Small-Outline (DB), and Thin Shrink Small-Outline (PW) Packages, Ceramic Chip Carriers (FK), Ceramic Flat (W) Packages, and Ceramic (J) DIPs

	DB, DW, OR PW PACKAGE
	(TOP VIEW)
1 <mark>OE</mark>	

	2Y4 1A1 1 <u>0E</u> 2 <u>0E</u> 2 <u>0E</u>	
1A2 2Y3	3 2 1 20 19 4 18	[ 1Y1
2Y3	5 17	2A4
1A3	6 16	[ 1Y2
2Y2 1A4	7 15	
1A4	8 14	[ 1Y3
	9 10 11 12 13	
	2Y1 GND 2A1 1Y4 2A2	

#### description

These octal buffers and line drivers are designed specifically for low-voltage (3.3-V) V<sub>CC</sub> operation, but with the capability to provide a TTL interface to a 5-V system environment.

The 'LVT244B is organized as two 4-bit line drivers with separate output-enable ( $\overline{OE}$ ) inputs. When  $\overline{OE}$  is low, the device passes data from the A inputs to the Y outputs. When  $\overline{OE}$  is high, the outputs are in the high-impedance state.

When  $V_{CC}$  is between 0 and 1.5 V, the device is in the high-impedance state during power up or power down. However, to ensure the high-impedance state above 1.5 V, OE should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sinking capability of the driver.

These devices are fully specified for hot-insertion applications using Ioff and power-up 3-state. The Ioff circuitry disables the outputs, preventing damaging current backflow through the devices when they are powered down. The power-up 3-state circuitry places the outputs in the high-impedance state during power up and power down, which prevents driver conflict.

The SN54LVT244B is characterized for operation over the full military temperature range of -55°C to 125°C. The SN74LVT244B is characterized for operation from -40°C to 85°C.



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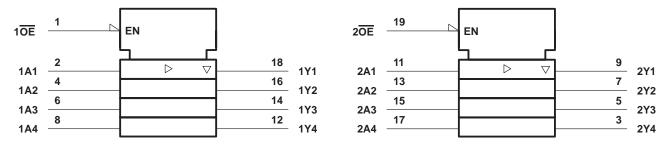


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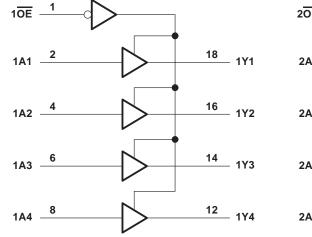
FUNCTION TABLE (each 4-bit buffer)								
INPUTS OUTPUT								
OE	Α	Y						
L	Н	Н						
L	L	L						
Н	Х	Z						

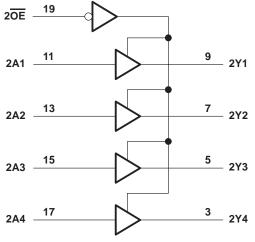
## logic symbol<sup>†</sup>



<sup>†</sup> This symbol is in accordance with ANSI/IEEE Std 91-1984 and IEC Publication 617-12.

## logic diagram (positive logic)







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## absolute maximum ratings over operating free-air temperature range (unless otherwise noted)<sup>†</sup>

Supply voltage range, V <sub>CC</sub> 0.5 V to 4.6 Input voltage range, V <sub>I</sub> (see Note 1)0.5 V to 7 Voltage range applied to any output in the high-impedance	
or power-off state, V <sub>O</sub> (see Note 1)	V
Voltage range applied to any output in the high state, V <sub>O</sub> (see Note 1)0.5 V to V <sub>CC</sub> + 0.5	V
Current into any output in the low state, I <sub>O</sub> : SN54LVT244B	۱A
SN74LVT244B	hΑ
Current into any output in the high state, I <sub>O</sub> (see Note 2): SN54LVT244B	nΑ
SN74LVT244B	hΑ
Input clamp current, I <sub>IK</sub> (V <sub>I</sub> < 0)	nΑ
Output clamp current, $I_{OK}$ (V <sub>O</sub> < 0)	hΑ
Package thermal impedance, $\theta_{JA}$ (see Note 3): DB package	W
DW package	W
PW package	
Storage temperature range, T <sub>stg</sub> –65°C to 150°	

<sup>†</sup> Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

- NOTES: 1. The input and output negative-voltage ratings may be exceeded if the input and output clamp-current ratings are observed.
  - 2. This current flows only when the output is in the high state and  $V_{O} > V_{CC}$ .
  - 3. The package thermal impedance is calculated in accordance with JESD 51.

### recommended operating conditions (see Note 4)

		SN54LV	T244B	SN74LV	UNIT		
			MIN	MAX	MIN	MAX	
V <sub>CC</sub> Supply voltage				3.6	2.7	3.6	V
VIH	High-level input voltage				2		V
VIL	Low-level input voltage					0.8	V
VI	Input voltage	4	5.5		5.5	V	
ЮН	H High-level output current					-32	mA
IOL	Low-level output current		202	48		64	mA
Δt/Δv	Input transition rise or fall rate	Outputs enabled	20%	10		10	ns/V
Δt/ΔV <sub>CC</sub>	Power-up ramp rate		<b>Q</b> 200		200		μs/V
TA	Operating free-air temperature				-40	85	°C

NOTE 4: All unused inputs of the device must at V<sub>CC</sub> or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.



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#### electrical characteristics over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER		TECT CO	SN54	4LVT244	В	SN74						
		TEST COI	MIN	TYP <sup>†</sup>	MAX	MIN	TYP <sup>†</sup>	MAX	UNIT			
		V <sub>CC</sub> = 2.7 V,	lj = -18 mA			-1.2			-1.2	V		
		V <sub>CC</sub> = 2.7 V to 3.6 V,	I <sub>OH</sub> = -100 μA	V <sub>CC</sub> -0.2			V <sub>CC</sub> -0.2					
		V <sub>CC</sub> = 2.7 V,	I <sub>OH</sub> =8 mA	2.4			2.4			V		
Vон		V <sub>CC</sub> = 3 V	I <sub>OH</sub> = -24 mA	2								
		vCC = 3 v	I <sub>OH</sub> = -32 mA				2					
			I <sub>OL</sub> = 100 μA			0.2			0.2			
		$V_{CC} = 2.7 V$	I <sub>OL</sub> = 24 mA			0.5			0.5			
V <sub>OL</sub>			I <sub>OL</sub> = 16 mA			0.4			0.4	V		
			I <sub>OL</sub> = 32 mA			0.5			0.5	v		
		$V_{CC} = 3 V$	I <sub>OL</sub> = 48 mA			0.55						
			I <sub>OL</sub> = 64 mA		N				0.55			
		V <sub>CC</sub> = 0 or 3.6 V,	V <sub>I</sub> = 5.5 V		ľ,	10			10	1 μA		
ı.	Control inputs	V <sub>CC</sub> = 3.6 V,	$V_I = V_{CC} \text{ or } GND$		R	±1			±1			
łı	Data inputs	V <sub>CC</sub> = 3.6 V	$V_I = V_{CC}$		1	1			1			
	Data inputs		$V_{I} = 0$		5	-5			-5			
loff		$V_{CC} = 0,$	$V_{I} \text{ or } V_{O} = 0 \text{ to } 4.5 \text{ V}$	0					±100	μΑ		
IOZH		V <sub>CC</sub> = 3.6 V,	$V_{O} = 3 V$	Q		5			5	μΑ		
IOZL		V <sub>CC</sub> = 3.6 V,	$V_{O} = 0.5 V$			-5			-5	μΑ		
IOZPL	J	$\frac{V_{CC}}{OE} = 0$ to 1.5 V, $V_{O} = 0$	0.5 V to 3 V,			±100*			±100	μA		
IOZPD		$\frac{V_{CC}}{OE}$ = 1.5 V to 0, V <sub>O</sub> = OE = don't care	0.5 V to 3 V,			±100*			±100	μΑ		
Icc		V <sub>CC</sub> = 3.6 V,	Outputs high			0.19			0.19			
		$I_{O} = 0,$	Outputs low			5			5	mA		
		$V_{I} = V_{CC}$ or GND	Outputs disabled			0.19			0.19			
∆l <sub>CC</sub> ‡		$V_{CC}$ = 3 V to 3.6 V, On Other inputs at $V_{CC}$ or	e input at V <sub>CC</sub> – 0.6 V, GND			0.3			0.2	mA		
Ci		V <sub>I</sub> = 3 V or 0			4			4		pF		
Co		V <sub>O</sub> = 3 V or 0			7			7		pF		

\* On products compliant to MIL-PRF-38535, this parameter is not production tested.

<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V, T<sub>A</sub> = 25°C.

<sup>‡</sup>This is the increase in supply current for each input that is at the specified TTL voltage level rather than V<sub>CC</sub> or GND.



## SN54LVT244B, SN74LVT244B 3.3-V ABT OCTAL BUFFERS/DRIVERS WITH 3-STATE OUTPUTS SCAS354F – FEBRUARY 1994 – REVISED APRIL 2000

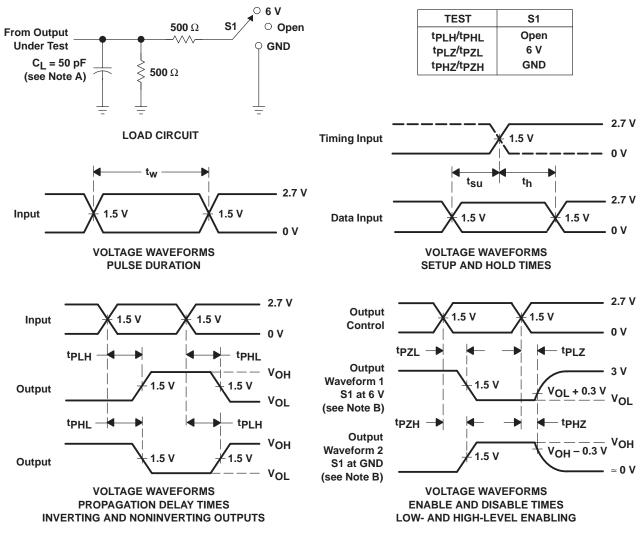
# switching characteristics over recommended operating free-air temperature range, $C_L = 50 \text{ pF}$ (unless otherwise noted) (see Figure 1)

				SN54L	/T244B			SN7	74LVT24	4B		
PARAMETER	AMETER FROM TO (INPUT) (OUT)		V <sub>CC</sub> = 3.3 V ± 0.3 V		<sup>3</sup> V V <sub>CC</sub> = 2.7 V		V <sub>CC</sub> = 3.3 V ± 0.3 V			V <sub>CC</sub> = 2.7 V		UNIT
			MIN	MAX	MIN	MAX	MIN	TYP <sup>†</sup>	MAX	MIN	MAX	
<sup>t</sup> PLH	A	V	1	3.6	1/2	3.9	1.1	2.3	3.5		3.8	ns
<sup>t</sup> PHL		A	I	1.2	3.4	24	3.6	1.3	2.1	3.3		3.6
<sup>t</sup> PZH	OE	×	1	4.6	2	5.5	1.1	2.5	4.5		5.3	ns
<sup>t</sup> PZL		I	1.3	4.5		5.1	1.4	2.7	4.4		4.9	115
<sup>t</sup> PHZ	OE	v	1.8	4.5		4.7	1.9	2.8	4.4		4.5	ns
<sup>t</sup> PLZ		OE	ſ	1.7	<b>4</b> .5		4.6	1.8	2.9	4.4		4.4

<sup>†</sup> All typical values are at V<sub>CC</sub> = 3.3 V,  $T_A = 25^{\circ}C$ .



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### PARAMETER MEASUREMENT INFORMATION

NOTES: A. CL includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- waveform 2 is for an output with internal conditions such that the output is high except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR  $\leq$  10 MHz, Z<sub>O</sub> = 50  $\Omega$ , t<sub>f</sub>  $\leq$  2.5 ns, t<sub>f</sub>  $\leq$  2.5 ns.

D. The outputs are measured one at a time with one transition per measurement.

Figure 1. Load Circuit and Voltage Waveforms



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